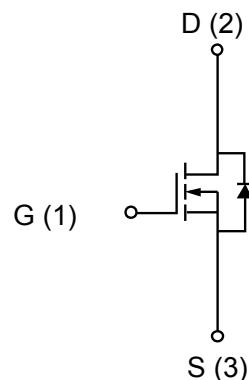


Description

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

MOSFET Product Summary		
V _{DS} (V)	R _{DS(on)} (mΩ)	I _D (A)
30	4@V _{GS} =10V	80



Absolute maximum rating@25°C

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current- Continuous(T _J =150°C)*	I _D	80	A
T _A =70°C	I _D	47	
Drain Current-Pulsed	I _{DM}	240	A
Maximum Power Dissipation*	P _D	42	W
T _A =70°C	P _D	27	
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C
Thermal Resistance, Junction-to-Case	R _{θJC}	3.0	°C/W

*The device mounted on 1in² FR4 board with 2 oz copper

Electrical characteristics per line@25°C(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	30		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±10	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1		3	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =15A	-	7	9	mΩ
		V _{GS} =10V, I _D =30A		4	4.8	
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =2.7A		0.8		V
Dynamic						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1.0MHz		2400	2700	pF
Output Capacitance	C _{oss}			350		
Reverse Transfer Capacitance	C _{rss}			110		
Gate Resistance	R _g	f=1MHz		0.9		Ω
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =17A		53	60	nC
Total Gate Charge	Q _g			27		
Gate-Source Charge	Q _{gs}			11		
Gate-Drain Charge	Q _{gd}			14		
Turn-On Delay Time	t _{d(on)}	V _{DD} =15V, V _{GEN} =10V, R _G =6Ω, R _L =15Ω, I _D =1.0A	-	23	30	ns
Turn-Off Delay Time	t _{d(off)}		-	76	100	
Turn-On Rise Time	t _r		-	17	22	
Turn-On Fall Time	t _f		-	15	20	

Typical Characteristics

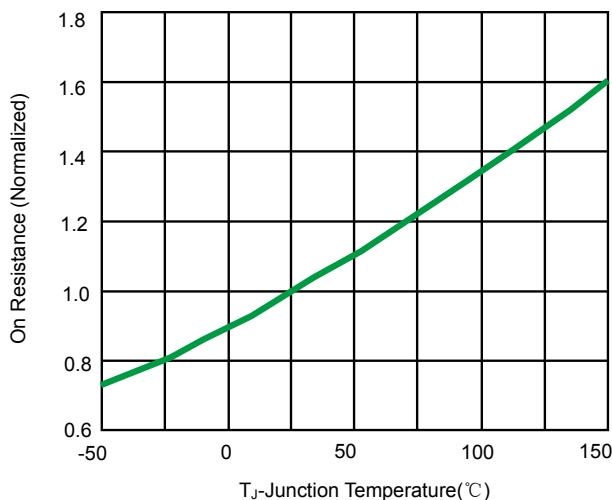


Fig 1. On Resistance vs. Junction Temperature

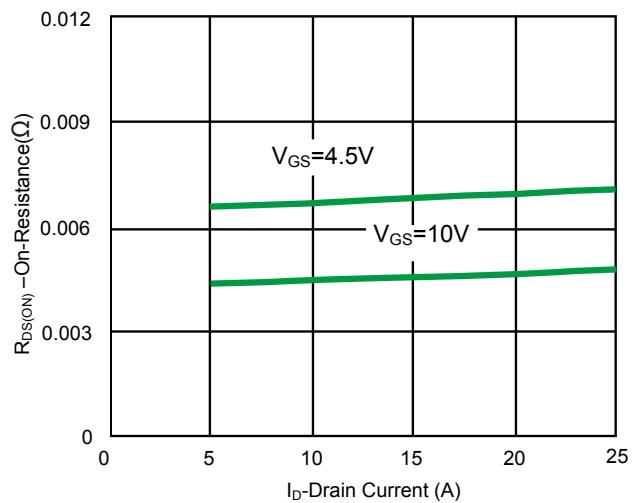


Fig 2. On-Resistance vs. Drain Current

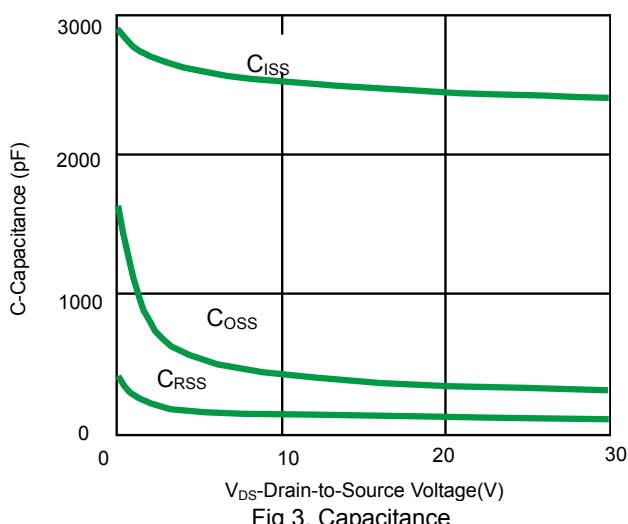


Fig 3. Capacitance

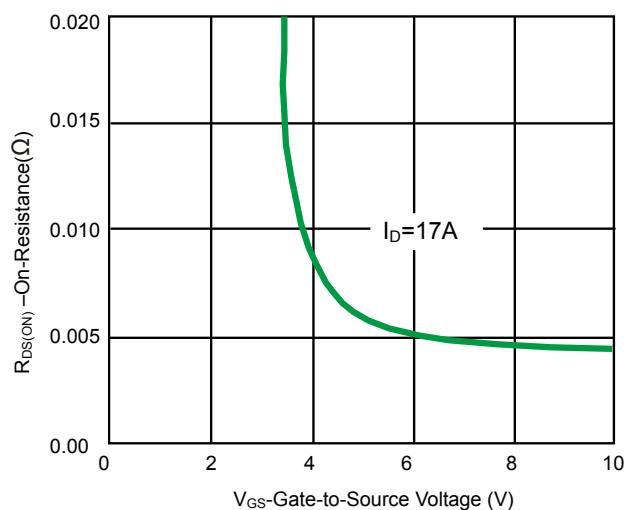


Fig 4. On-Resistance vs. Gate-to-Source Voltage

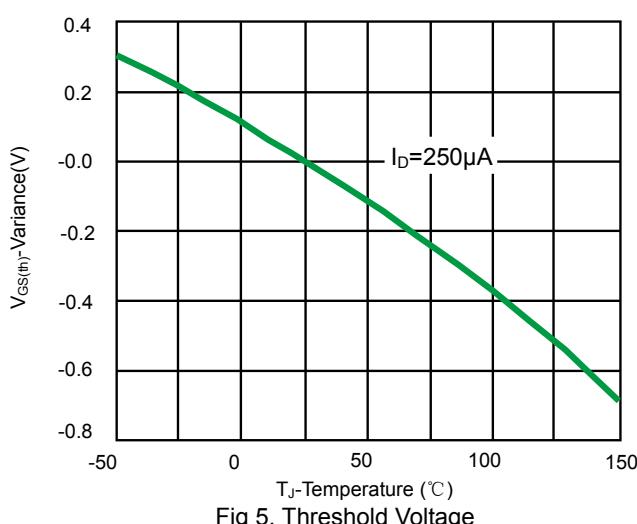


Fig 5. Threshold Voltage

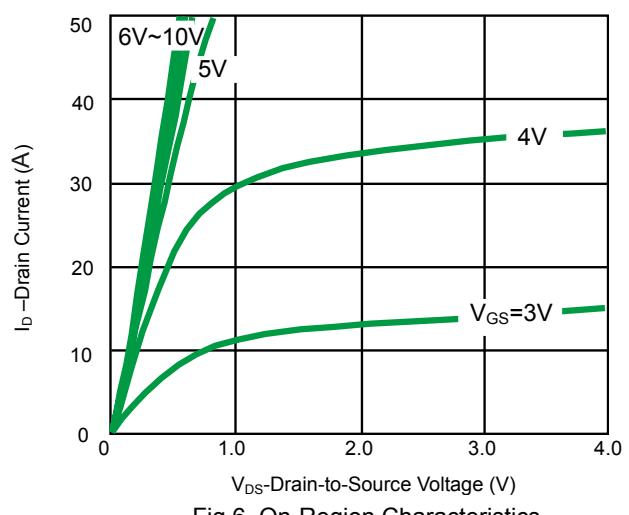


Fig 6. On-Region Characteristics

N-Channel MOSFET

PNMDP30V90

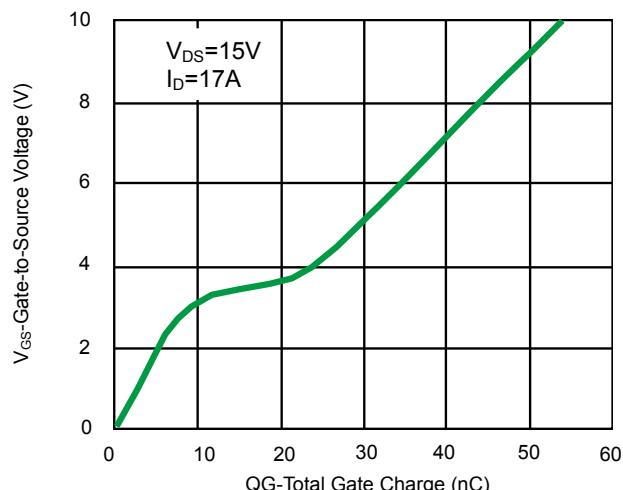


Fig 7. Gate Charge

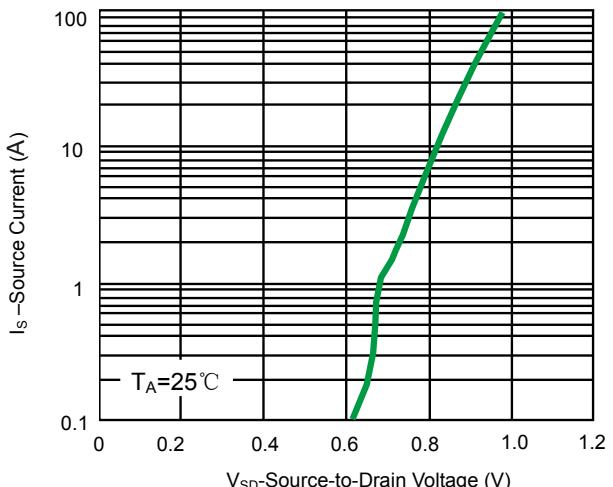
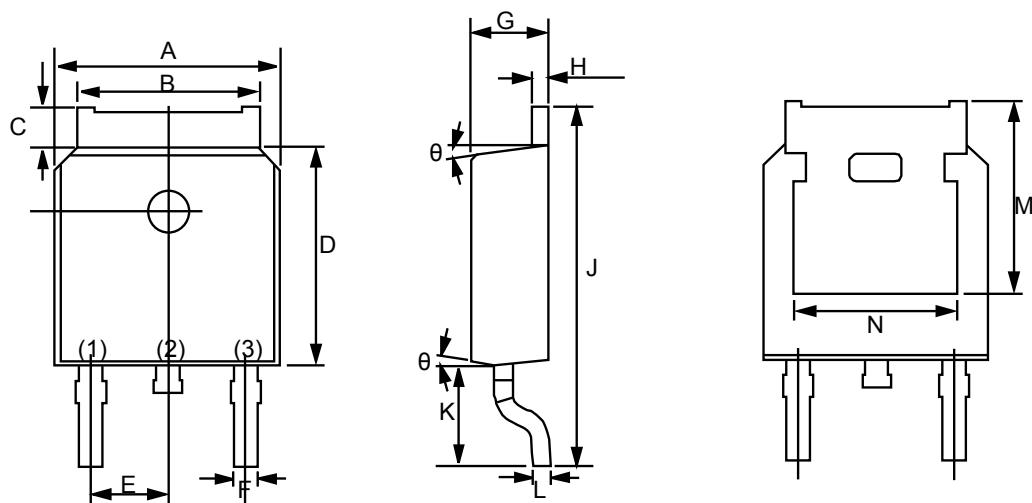


Fig 8. Source to Drain Diode Forward Voltage

Product dimension(TO-252)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	6.50	6.70	0.255	0.263
B	5.23	5.46	0.205	0.214
C	0.90	1.25	0.035	0.049
D	6.00	6.20	0.236	0.244
E	2.286BSC.		0.09BSC.	
F	0.72	0.85	0.028	0.033
G	2.20	2.38	0.086	0.093
H	0.47	0.58	0.018	0.022
J	9.90	10.30	0.389	0.405
K	2.90REF.		0.114REF.	
L	0.51BSC.		0.020BSC.	
M	5.30REF.		0.208REF.	
N	4.70	4.92	0.185	0.193
θ	5°	9°	5°	9°

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